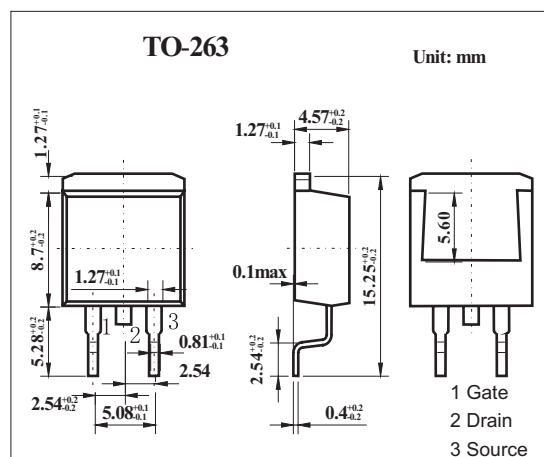
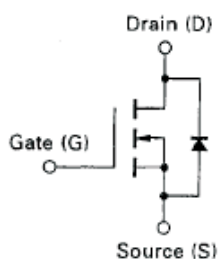


MOS Field Effect Power Transistor

2SK2133

■ Features

- Low on-resistance
 $R_{DS(on)}=0.21\ \Omega\ \text{MAX.}@V_{GS}=10V, I_D=8.0A$
- Low Ciss Ciss=1090 pF TYP.
- High avalanche capabil



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	250	V
Gate to source voltage	V_{GS}	± 30	V
Drain current	I_D	± 16	A
	I_{DP}^*	± 64	A
Power dissipation $T_a=25^\circ\text{C}$ $T_c=25^\circ\text{C}$	P_D	1.5	W
		75	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\ \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=250V, V_{GS}=0$			100	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0$			± 10	μA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1\text{mA}$	2.0		4.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=8.0A$	4.0			S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8.0A$		0.2	0.26	Ω
Input capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1\text{MHz}$		1090		pF
Output capacitance	C_{oss}			420		pF
Reverse transfer capacitance	C_{rss}			80		pF
Turn-on delay time	$t_{d(on)}$	$I_D=8.0A, V_{GS(on)}=10V, R_L=18.75\ \Omega, R_G=10\ \Omega, V_{DD}=150V$		20		ns
Rise time	t_r			40		ns
Turn-off delay time	$t_{d(off)}$			60		ns
Fall time	t_f			20		ns